JJMICROELECTRONICS

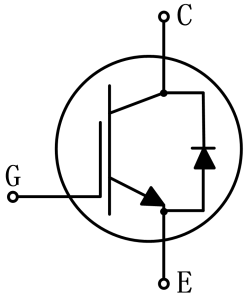
650V 30A T c a d F d S IGBT

JJT30N65SC

TO-263

- $_{CE}$=650V
- $_{C}$=30A@ $_{C}$=100
- $_{CE(\ )}$=1.7 V

- H .
- 10 .
- P $_{CE(\ )}$.
- H .
- E .
- R HS .



- H
- M
- G

T	M	P	P
JJT30N65SC	T3065SC	TO-263	T

CES	C -	650	V
GES	G -	20	V
C	C (C=25)	60	A
	C (C=100)	30	A
CM	P ,	120	A
F	D (C=100)	30	A
FM	D ,	80	A
	S	10	
	P (C=25)	250	
	P (C=100)	125	
	O	-40 +175	
	S	-55 +150	

(-)	T , IGBT	-	0.6	K/
(-)	T , D	-	1.1	K/
(-)	T ,	-	40	K/

(=25)

S

CES	C -	GE=0V, C=250 A	650	-	-	V
CES	C -	CE=650V, GE=0V	-	-	50	A
GES	G ,	GE=20V, CE=0V	-	-	100	A
	G ,	GE=-20V, CE=0V	-	-	-100	A
GE( )	G -	GE= CE, C=1 A	5.2	5.7	6.2	V
CE( )	C -	GE=15V, C=30A	-	1.7	-	V
		GE=15V, C=30A, =175	-	2.2	-	V

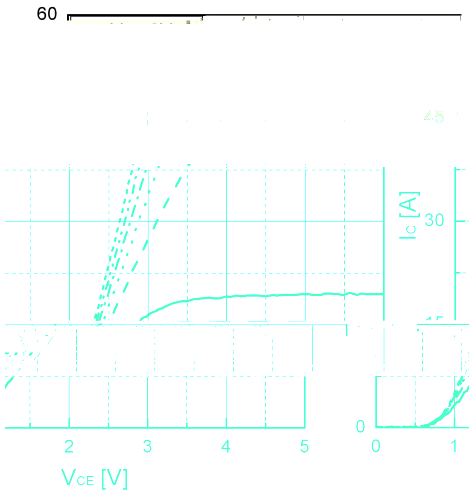
D

	I	CE=30V GE=0V =1MH	-	1978	-	F
	O		-	100	-	F
	R		-	23	-	F
	T	CC=520V GE=15V C=30A	-	103	-	C

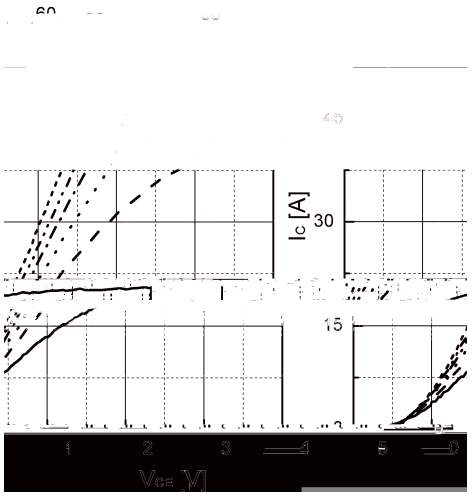
A d c i f ai i c igh ed a d b ec ega di c ai e .

(=25)

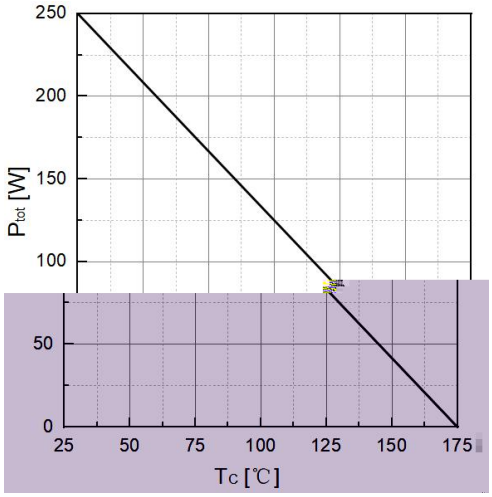
F	D	$_F$=30A	-	1.7	-	V
		$_F$=30A, =175	-	1.4	-	V
	D	$_R$=400V $_F$=30A $_F$/ =-550A/	-	105	-	
	D		-	16	-	A
	D		-	876	-	C
	D	$_R$=400V $_F$=30A $_F$/ =-550A/ =175	-	171	-	
	D		-	26	-	A
	D		-	2650	-	C



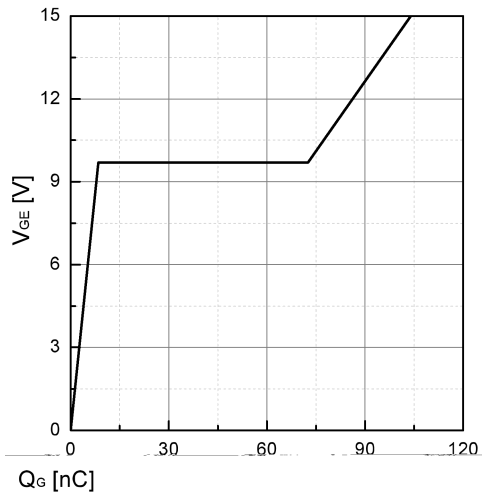
F 1. T (=25)



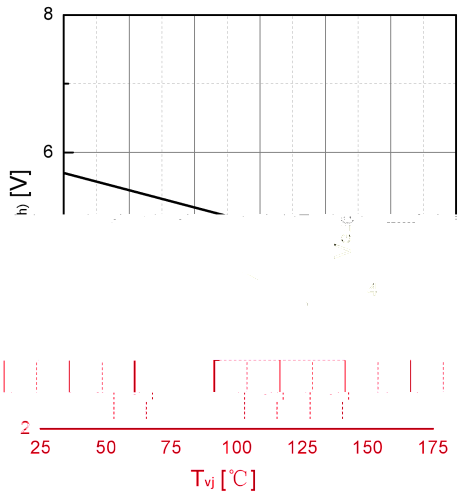
F 2. T (=175)



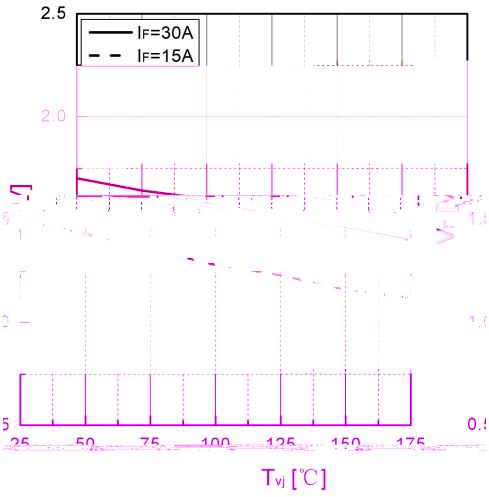
F 3. P



F 4. T G

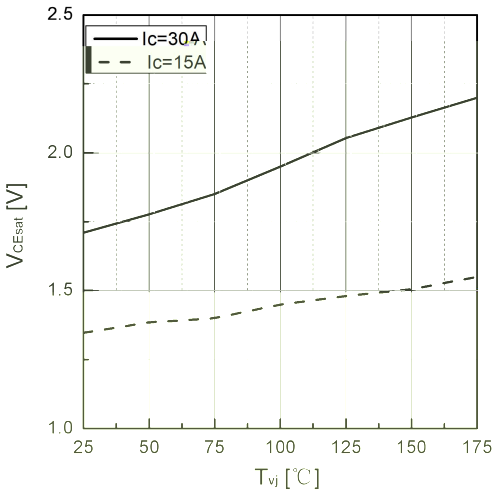


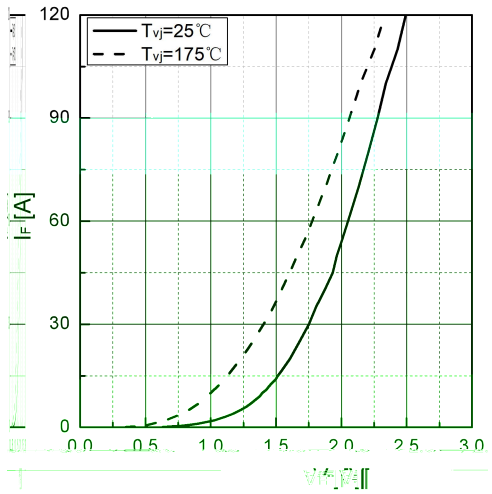
F 5. T GE( )
(C=1 A)



F 6. T F

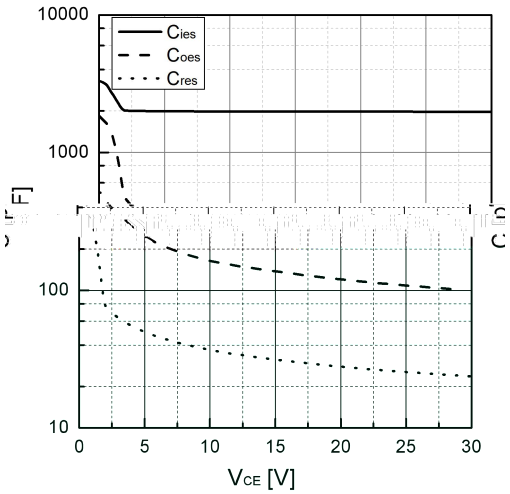
A d c i f ai i c igh ed a d b ec ega di c ai e .



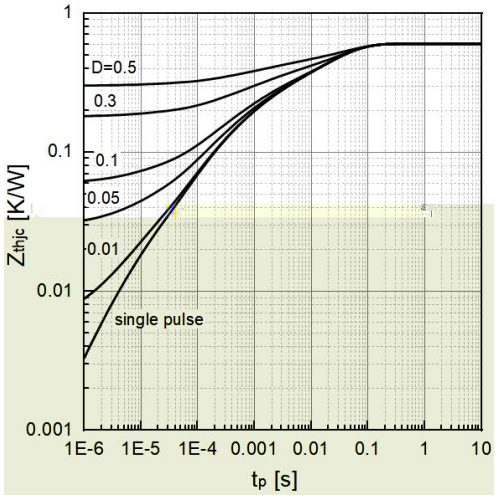


F 7. T CE

A d c i f ai i c igh ed a d bec ega di c ai e .



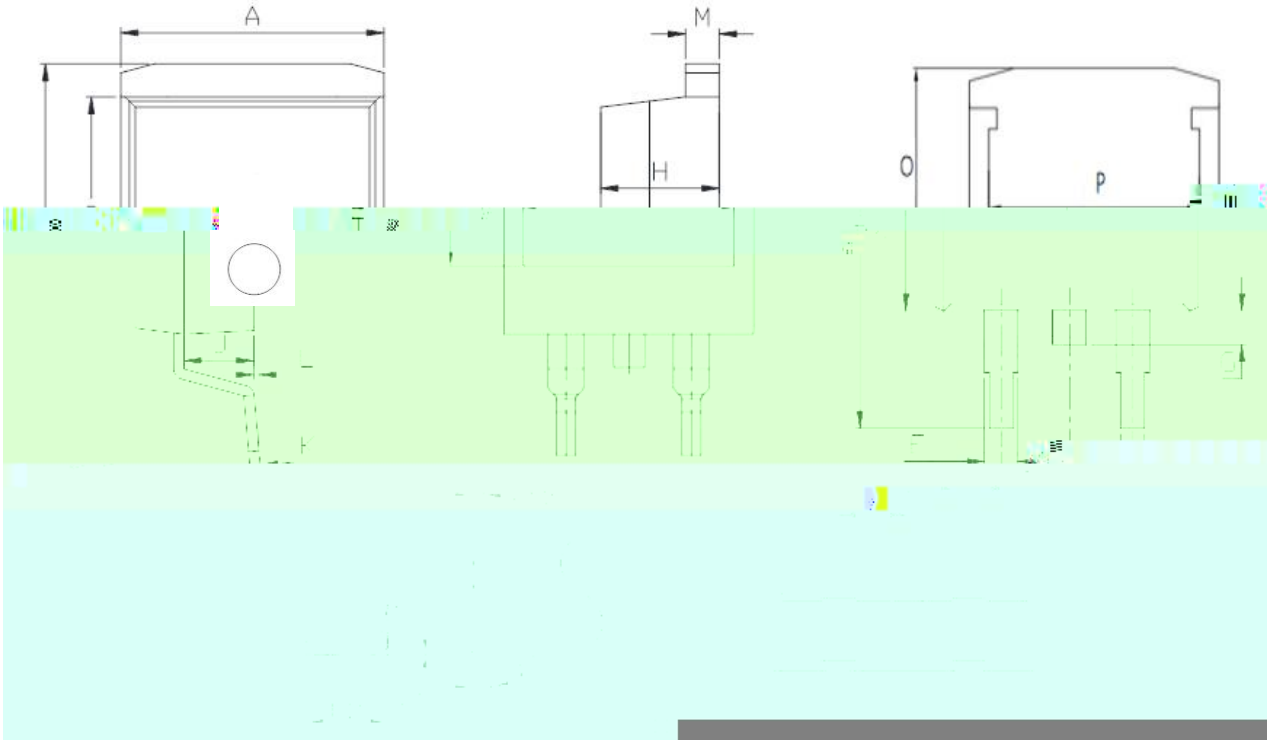
F 13. T CE
(=1M , GE=0V)



F 14. T , IGBT

A d c i f ai i c igh ed a d b ec ega di c ai e .

TO-263



R .	D					
	M			I		
	M .	T .	M .	M .	T .	M .
A	9.90	-	10.20	0.390	-	0.402
B	14.70	-	15.80	0.579	-	0.622
C	8.8	-	9.4	0.346	-	0.370
D	-	2.54	-	-	0.100	-
E	1.37	-	1.57	0.054	-	0.062
F	0.75	-	0.85	0.029	-	0.033
G	-	-	1.75	-	-	0.069
H	4.30	-	4.70	0.169	-	0.185
J	2.30	-	2.70	0.091	-	0.106
K	0.38	-	0.55	0.015	-	0.022
L	0	0.15	0.25	0	0.006	0.010
M	1.25	-	1.35	0.049	-	0.053
O	7.4	7.65	7.9	0.291	0.301	0.311
P	8.3	8.6	8.9	0.327	0.339	0.350
L2	2.20	2.35	2.50	0.087	0.093	0.098

A d c i f ai i c igh ed a d b ec ega di c ai e .

A dcif ai ic ighed a d bec ega di cai e .